

Amendments to the Specification:

Please amend the paragraph beginning on page 8, line 11 as follows:

FIG. 1 is a view showing a ferroelectric capacitor in a ferroelectric memory device in the present embodiment. In FIG. 1, 101 denotes a PZTN ferroelectric film according to the present invention, 102 denotes a first electrode, and 103 denotes a second electrode. The ferroelectric film may include silicon, or silicon and germanium, in elements of ferroelectric. The first electrode 102 and the second electrode 103 are formed of a noble metal element such as Pt, Ir, or Ru, or a composite material containing the noble metal as a major component. If the element of the ferroelectric is diffused into the first electrode, squareness of hysteresis is decreased due to composition variation at the interface between the electrode and the ferroelectric film. Therefore, the first electrode must have a density which does not allow the element of the ferroelectric to diffuse into the first electrode. In order to increase the density of the first electrode, a method of depositing the first electrode by sputtering using a heavy gas, or a method of dispersing an oxide of Y, La, or the like into the noble metal electrode is used, for example. In FIG. 1, the substrate and other constituent elements (MOS transistors and the like) of the ferroelectric memory device are omitted. These constituent elements are described later.